

# Hideto Miyake

## List of Publications by Citations

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249  
papers

3,931  
citations

29  
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52  
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270  
ext. papers

4,439  
ext. citations

2.1  
avg, IF

5.36  
L-index

#	Paper	IF	Citations
249	Fabrication and characterization of low defect density GaN using facet-controlled epitaxial lateral overgrowth (FACELO). <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 316-326	1.6	364
248	Recent Progress in Selective Area Growth and Epitaxial Lateral Overgrowth of III-Nitrides: Effects of Reactor Pressure in MOVPE Growth. <i>Physica Status Solidi A</i> , <b>1999</b> , 176, 535-543		232
247	Preparation of high-quality AlN on sapphire by high-temperature face-to-face annealing. <i>Journal of Crystal Growth</i> , <b>2016</b> , 456, 155-159	1.6	165
246	Annealing of an AlN buffer layer in N <sub>2</sub> O for growth of a high-quality AlN film on sapphire. <i>Applied Physics Express</i> , <b>2016</b> , 9, 025501	2.4	139
245	AlGaIn-based deep UV LEDs grown on sputtered and high temperature annealed AlN/sapphire. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 041110	3.4	136
244	Effects of sodium on electrical properties in Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 152101	3.4	100
243	Effects of Reactor Pressure on Epitaxial Lateral Overgrowth of GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, L1000-L1002	1.4	88
242	Sharp band edge photoluminescence of high-purity CuInS <sub>2</sub> single crystals. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 742-744	3.4	74
241	Impacts of Si-doping and resultant cation vacancy formation on the luminescence dynamics for the near-band-edge emission of Al <sub>0.6</sub> Ga <sub>0.4</sub> N films grown on AlN templates by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 213506	2.5	73
240	Optical constants of CuGaSe <sub>2</sub> and CuInSe <sub>2</sub> . <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 5202-5209	2.5	68
239	Correlation between intrinsic defects and electrical properties in the high-quality Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 112107	3.4	67
238	Optical and Crystalline Properties of Epitaxial-Lateral-Overgrown-GaN Using Tungsten Mask by Hydride Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, L356-L359	1.4	60
237	Preparation of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals from Sn solutions. <i>Journal of Crystal Growth</i> , <b>2012</b> , 341, 38-41	1.6	59
236	Fabrication of Deep-Ultraviolet-Light-Source Tube Using Si-Doped AlGaIn. <i>Applied Physics Express</i> , <b>2011</b> , 4, 042103	2.4	52
235	Formation of GaN Self-Organized Nanotips by Reactive Ion Etching. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, L1301-L1304	1.4	51
234	Improvement mechanism of sputtered AlN films by high-temperature annealing. <i>Journal of Crystal Growth</i> , <b>2018</b> , 502, 41-44	1.6	50
233	Native cation vacancies in Si-doped AlGaIn studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 013512	2.5	45

232	High-quality AlN epitaxial films on (0001)-faced sapphire and 6H-SiC substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2003</b> , 2023-2026		45
231	Reduction of threading dislocation density and suppression of cracking in sputter-deposited AlN templates annealed at high temperatures. <i>Applied Physics Express</i> , <b>2019</b> , 12, 065501	2.4	43
230	Room-temperature operation of AlGaIn ultraviolet-B laser diode at 298 nm on lattice-relaxed Al <sub>0.6</sub> Ga <sub>0.4</sub> N/AlN/sapphire. <i>Applied Physics Express</i> , <b>2020</b> , 13, 031004	2.4	40
229	Growth of Cu <sub>2</sub> ZnSnSe <sub>4</sub> single crystals from Sn solutions. <i>Journal of Crystal Growth</i> , <b>2012</b> , 354, 147-151	1.6	40
228	Growth of Crack-Free and High-Quality AlGaIn with High Al Content Using Epitaxial AlN (0001) Films on Sapphire. <i>Physica Status Solidi A</i> , <b>2002</b> , 194, 498-501		38
227	Dependence of internal quantum efficiency on doping region and Si concentration in Al-rich AlGaIn quantum wells. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 042110	3.4	37
226	Impact of high-temperature annealing of AlN layer on sapphire and its thermodynamic principle. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 05FL02	1.4	36
225	Low-pressure HVPE growth of crack-free thick AlN on a trench-patterned AlN template. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 2831-2833	1.6	36
224	High-quality and highly-transparent AlN template on annealed sputter-deposited AlN buffer layer for deep ultra-violet light-emitting diodes. <i>AIP Advances</i> , <b>2017</b> , 7, 055110	1.5	35
223	Growth of Thick AlN Layer by Hydride Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L505-L507	1.4	35
222	Selective Area Growth of GaN Using Tungsten Mask by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, L845-L848	1.4	35
221	Reactor-pressure dependence of growth of a-plane GaN on r-plane sapphire by MOVPE. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4979-4982	1.6	31
220	Deep Ultraviolet Light Source from Ultrathin GaN/AlN MQW Structures with Output Power Over 2 Watt. <i>Advanced Optical Materials</i> , <b>2019</b> , 7, 1801763	8.1	29
219	Growth of High-Quality AlN and AlGaIn Films on Sputtered AlN/Sapphire Templates via High-Temperature Annealing. <i>Physica Status Solidi (B): Basic Research</i> , <b>2018</b> , 255, 1700506	1.3	26
218	Suppression of dislocation-induced spiral hillocks in MOVPE-grown AlGaIn on face-to-face annealed sputter-deposited AlN template. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 062101	3.4	25
217	Transmission Electron Microscopy Investigation of Dislocations in GaN Layer Grown by Facet-Controlled Epitaxial Lateral Overgrowth. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, L309-L312	1.4	24
216	Growth of CuGaSe <sub>2</sub> single crystals by the traveling heater method. <i>Journal of Crystal Growth</i> , <b>1989</b> , 98, 610-616	1.6	24
215	Growth and Characterization of AlGaIn Multiple Quantum Wells for Electron-Beam Target for Deep-Ultraviolet Light Sources. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 01AF03	1.4	23

214	Growth and characterization of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2013</b> , 210, 1328-1331	1.6	22
213	THM growth and properties of CuInSe <sub>2</sub> single crystals. <i>Journal of Crystal Growth</i> , <b>1992</b> , 125, 548-552	1.6	22
212	Photoluminescence of CuAl <sub>x</sub> Ga <sub>1-x</sub> Se <sub>2</sub> crystals grown by chemical vapor transport. <i>Journal of Applied Physics</i> , <b>1989</b> , 65, 5212-5215	2.5	22
211	Reduction in the concentration of cation vacancies by proper Si-doping in the well layers of high AlN mole fraction Al <sub>x</sub> Ga <sub>1-x</sub> N multiple quantum wells grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 121602	3.4	21
210	Photoreflectance of CuInS <sub>2</sub> single crystal prepared by traveling heater method. <i>Journal of Physics and Chemistry of Solids</i> , <b>2003</b> , 64, 2021-2024	3.9	21
209	Ultraviolet-B band lasers fabricated on highly relaxed thick Al <sub>0.55</sub> Ga <sub>0.45</sub> N films grown on various types of AlN wafers. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SC1052	1.4	20
208	Quantitative evaluation of strain relaxation in annealed sputter-deposited AlN film. <i>Journal of Crystal Growth</i> , <b>2019</b> , 512, 16-19	1.6	19
207	Inhomogeneous distribution of defect-related emission in Si-doped AlGa <sub>N</sub> epitaxial layers with different Al content and Si concentration. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 053509	2.5	19
206	Photoluminescence study of Si-doped a-plane GaN grown by MOVPE. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 2906-2909	1.6	19
205	Nitriding r-plane sapphire to improve crystal qualities and surface morphologies of a-plane GaN grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 121910	3.4	19
204	TEM analysis of threading dislocations in crack-free Al <sub>x</sub> Ga <sub>1-x</sub> N grown on an AlN(0001) template. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2003</b> , 2444-2447		19
203	Growth and characterization of Cu <sub>2</sub> ZnSn(S <sub>1-x</sub> Se <sub>x</sub> ) <sub>4</sub> alloys grown by the melting method. <i>Journal of Crystal Growth</i> , <b>2014</b> , 386, 204-207	1.6	18
202	Structural and electrical properties of Si-doped a-plane GaN grown on r-plane sapphire by MOVPE. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 2899-2902	1.6	18
201	Effects of initial stages on the crystal quality of nonpolar a-plane AlN on r-plane sapphire by low-pressure HVPE. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 3801-3805	1.6	18
200	Transmission Electron Microscopy Characterization of Position-Controlled InN Nanocolumns. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 5330-5332	1.4	18
199	Crystal Orientation Fluctuation of Epitaxial-Lateral-Overgrown GaN with W Mask and SiO <sub>2</sub> Mask Observed by Transmission Electron Diffraction and X-Ray Rocking Curves. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, L1299-L1302	1.4	18
198	Epitaxial growth of CuAlSe <sub>2</sub> on CuGaSe <sub>2</sub> substrates. <i>Journal of Crystal Growth</i> , <b>1991</b> , 113, 390-394	1.6	18
197	Growth of CuGaS <sub>2</sub> Single Crystals by Traveling Heater Method. <i>Japanese Journal of Applied Physics</i> , <b>1990</b> , 29, L1859-L1861	1.4	18

196	Thermo-physical properties of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. <i>Journal of Crystal Growth</i> , <b>2014</b> , 393, 167-170	1.6	17
195	Influence of off-cut angle of r-plane sapphire on the crystal quality of nonpolar a-plane AlN by LP-HVPE. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 4473-4477	1.6	17
194	Effect of strain on quantum efficiency of InAlN-based solar-blind photodiodes. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 083504	3.4	17
193	High temperature growth of AlN film by LP-HVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2007</b> , 4, 2252-2255		17
192	High Quality GaN Grown by Facet-Controlled ELO (FACELO) Technique. <i>Physica Status Solidi A</i> , <b>2002</b> , 194, 545-549		17
191	Optical properties of CuGaSe <sub>2</sub> and CuAlSe <sub>2</sub> layers epitaxially grown on Cu(In <sub>0.04</sub> Ga <sub>0.96</sub> )Se <sub>2</sub> substrates. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 7294-7302	2.5	17
190	Preparation of CuGaIn <sub>1-x</sub> S <sub>2</sub> alloys from In solutions. <i>Journal of Crystal Growth</i> , <b>1993</b> , 134, 174-180	1.6	17
189	Fabrication of high-crystallinity a-plane AlN films grown on r-plane sapphire substrates by modulating buffer-layer growth temperature and thermal annealing conditions. <i>Journal of Crystal Growth</i> , <b>2017</b> , 468, 845-850	1.6	16
188	Control of AlN buffer/sapphire substrate interface for AlN growth. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 2069-2071		16
187	Effects of Substrate Plane on the Growth of High Quality AlN by Hydride Vapor Phase Epitaxy. <i>Applied Physics Express</i> , <b>2009</b> , 2, 111004	2.4	16
186	Buried Tungsten Metal Structure Fabricated by Epitaxial-Lateral-Overgrown GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, L449-L452	1.4	16
185	Single Crystal Growth of Cu <sub>2</sub> Te <sub>2</sub> Semiconductors by THM. <i>Japanese Journal of Applied Physics</i> , <b>1993</b> , 32, 156	1.4	16
184	Low dislocation density AlN on sapphire prepared by double sputtering and annealing. <i>Applied Physics Express</i> , <b>2020</b> , 13, 095501	2.4	16
183	Internal loss of AlGaIn-based ultraviolet-B band laser diodes with p-type AlGaIn cladding layer using polarization doping. <i>Applied Physics Express</i> , <b>2020</b> , 13, 071008	2.4	15
182	AlN homoepitaxial growth on sublimation-AlN substrate by low-pressure HVPE. <i>Journal of Crystal Growth</i> , <b>2012</b> , 350, 69-71	1.6	14
181	Silicon concentration dependence of optical polarization in AlGaIn epitaxial layers. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 021910	3.4	14
180	Influence of growth interruption and Si doping on the structural and optical properties of Al <sub>x</sub> GaN/AlN (x>0.5) multiple quantum wells. <i>Journal of Crystal Growth</i> , <b>2007</b> , 298, 500-503	1.6	14
179	Suppression of Crack Generation Using High-Compressive-Strain AlN/Sapphire Template for Hydride Vapor Phase Epitaxy of Thick AlN Film. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L552-L555	1.4	14

178	Extraordinary Optical Transmission Exhibited by Surface Plasmon Polaritons in a Double-Layer Wire Grid Polarizer. <i>Plasmonics</i> , <b>2015</b> , 10, 1657-1662	2.4	13
177	Growth of High-Quality Si-Doped AlGa <sub>N</sub> by Low-Pressure Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 095502	1.4	13
176	Influence of growth conditions on Al incorporation to Al <sub>x</sub> Ga <sub>1-x</sub> N (x>0.4) grown by MOVPE. <i>Journal of Crystal Growth</i> , <b>2007</b> , 298, 372-374	1.6	13
175	High performance Schottky UV detectors (265–300 nm) using n-Al <sub>0.5</sub> Ga <sub>0.5</sub> N on AlN epitaxial layer. <i>Physica Status Solidi A</i> , <b>2003</b> , 200, 151-154		13
174	Distribution Profiles and Annealing Characteristics of Defects in GaAs Induced by Low-Energy FIB Irradiation. <i>Japanese Journal of Applied Physics</i> , <b>1988</b> , 27, L2037-L2039	1.4	13
173	Effects of carrier gas ratio and growth temperature on MOVPE growth of AlN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 499-502		12
172	Antireflection Effect of Self-Organized GaN Nanotip Structure from Ultraviolet to Visible Region. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, L1134-L1136	1.4	12
171	Vapor phase epitaxy of CuAlS <sub>2</sub> on CuGaS <sub>2</sub> substrates by the iodine transport method. <i>Journal of Crystal Growth</i> , <b>1995</b> , 153, 180-183	1.6	12
170	Photoluminescence characteristics of CuAl <sub>x</sub> In <sub>1-x</sub> Se <sub>2</sub> solid solutions grown by iodine transport technique. <i>Journal of Applied Physics</i> , <b>1992</b> , 72, 3697-3701	2.5	12
169	High-quality AlN/sapphire templates prepared by thermal cycle annealing for high-performance ultraviolet light-emitting diodes. <i>Applied Physics Express</i> , <b>2021</b> , 14, 035505	2.4	12
168	Improved quality of CuGaSe <sub>2</sub> and CuAlSe <sub>2</sub> epilayers grown on CuGa <sub>0.96</sub> In <sub>0.04</sub> Se <sub>2</sub> substrates. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 533-535	3.4	11
167	High Quality GaN Grown by Raised-Pressure HVPE. <i>Physica Status Solidi A</i> , <b>2002</b> , 194, 528-531		11
166	Electron Paramagnetic Resonance and Photoluminescence Study of Defects in CuGaSe <sub>2</sub> Single Crystals Grown by the Traveling Heater Method. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, 59-63	1.4	11
165	Photoreflectance of CuAl <sub>x</sub> In <sub>1-x</sub> Se <sub>2</sub> Alloys. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 77-78	1.4	11
164	AlGa <sub>N</sub> -based UV-B laser diode with a high optical confinement factor. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 163504	3.4	11
163	Fabrication of AlN templates on SiC substrates by sputtering-deposition and high-temperature annealing. <i>Journal of Crystal Growth</i> , <b>2019</b> , 510, 13-17	1.6	11
162	A design strategy for achieving more than 90% of the overlap integral of electron and hole wavefunctions in high-Al <sub>N</sub> -mole-fraction Al <sub>x</sub> Ga <sub>1-x</sub> N multiple quantum wells. <i>Applied Physics Express</i> , <b>2017</b> , 10, 015802	2.4	10
161	Preparation of high-quality thick AlN layer on nanopatterned sapphire substrates with sputter-deposited annealed AlN film by hydride vapor-phase epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SC1003	1.4	10

160	Growth and characterization of Cu <sub>2</sub> ZnSn(S Se) <sub>1-x</sub> single crystal grown by traveling heater method. <i>Journal of Crystal Growth</i> , <b>2015</b> , 423, 9-15	1.6	10
159	Effect of dislocation density on optical gain and internal loss of AlGaIn-based ultraviolet-B band lasers. <i>Applied Physics Express</i> , <b>2020</b> , 13, 045504	2.4	10
158	High Crystallinity and Highly Relaxed Al <sub>0.60</sub> Ga <sub>0.40</sub> N Films Using Growth Mode Control Fabricated on a Sputtered AlN Template with High-Temperature Annealing. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2020</b> , 217, 1900868	1.6	10
157	Orientation dependence of polarized Raman spectroscopy for nonpolar, semi-polar, and polar bulk GaN substrates. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 011909	3.4	10
156	AlN Grown on a- and n-Plane Sapphire Substrates by Low-Pressure Hydride Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 08JB31	1.4	10
155	Metalorganic Vapor Phase Epitaxy Growth and Study of Stress in AlGaIn Using Epitaxial AlN as Underlying Layer. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, L572-L574	1.4	10
154	Epitaxial lateral overgrowth of GaN on selected-area Si(1 1 1) substrate with nitrided Si mask. <i>Journal of Crystal Growth</i> , <b>2003</b> , 248, 573-577	1.6	10
153	Fabrication and Optical Characterization of Facet-Controlled ELO (FACELO) GaN by LP-MOVPE. <i>Physica Status Solidi A</i> , <b>2001</b> , 188, 725-728		10
152	Distribution of Threading Dislocations in Epitaxial Lateral Overgrowth GaN by Hydride Vapor-Phase Epitaxy Using Mixed Carrier Gas of H <sub>2</sub> and N <sub>2</sub> . <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 75-76	1.4	10
151	Influence of Ambient Gas on the Epitaxial Lateral Overgrowth of GaN by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi A</i> , <b>1999</b> , 176, 561-565		10
150	MOVPE growth of AlN films on nano-patterned sapphire substrates with annealed sputtered AlN. <i>Journal of Crystal Growth</i> , <b>2020</b> , 532, 125397	1.6	10
149	Annealing behaviors of vacancy-type defects in AlN deposited by radio-frequency sputtering and metalorganic vapor phase epitaxy studied using monoenergetic positron beams. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 085704	2.5	10
148	Cross-sectional X-ray microdiffraction study of a thick AlN film grown on a trench-patterned AlN/Al <sub>2</sub> O <sub>3</sub> template. <i>Journal of Crystal Growth</i> , <b>2013</b> , 381, 37-42	1.6	9
147	HVPE growth of AlN on trench-patterned 6H-SiC substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 467-469		9
146	Deep Electronic Levels of Al <sub>x</sub> Ga <sub>1-x</sub> N with a Wide Range of Al Composition Grown by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 101001	1.4	9
145	Mobility enhancement of 2DEG in MOVPE-grown AlGaIn/AlN/GaN HEMT structure using vicinal (0 0 1) sapphire. <i>Superlattices and Microstructures</i> , <b>2009</b> , 46, 812-816	2.8	9
144	Optical properties of MOVPE-grown a-plane GaN and AlGaIn. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 2903-2905	1.6	9
143	Growth of undoped and Zn-doped GaN nanowires. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 2970-2972	1.6	9

142	Blue emission from InGaN/GaN hexagonal pyramid structures. <i>Superlattices and Microstructures</i> , <b>2007</b> , 41, 341-346	2.8	9
141	Field Emission from GaN Self-Organized Nanotips. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, L1194-L1196	1.4	9
140	Growth of Bulk CuGaS <sub>2</sub> Single Crystals Using Solution Bridgman Method. <i>Japanese Journal of Applied Physics</i> , <b>1990</b> , 29, L1001-L1003	1.4	9
139	Impact of face-to-face annealed sputtered AlN on the optical properties of AlGa <sub>N</sub> multiple quantum wells. <i>AIP Advances</i> , <b>2019</b> , 9, 125342	1.5	9
138	Structural analysis of polarity inversion boundary in sputtered AlN films annealed under high temperatures. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SCCB30	1.4	8
137	Local and anisotropic strain in AlN film on sapphire observed by Raman scattering spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SCCB17	1.4	8
136	Using surface-plasmon polariton at the GaP-Au interface in order to detect chemical species in high-refractive-index media. <i>Optics Communications</i> , <b>2015</b> , 341, 64-68	2	8
135	Microscopic crystalline structure of a thick AlN film grown on a trench-patterned AlN/Al <sub>2</sub> O <sub>3</sub> template. <i>Journal of Crystal Growth</i> , <b>2015</b> , 411, 38-44	1.6	8
134	Correlation between in-plane strain and optical polarization of Si-doped AlGa <sub>N</sub> epitaxial layers as a function of Al content and Si concentration. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 033512	2.5	8
133	Huge binding energy of localized biexcitons in Al-rich Al <sub>x</sub> Ga <sub>1-x</sub> N ternary alloys. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 081907	3.4	8
132	Photoluminescence due to Inelastic Biexciton Scattering from an Al <sub>0.61</sub> Ga <sub>0.39</sub> N Ternary Alloy Epitaxial Layer at Room Temperature. <i>Applied Physics Express</i> , <b>2012</b> , 5, 072401	2.4	8
131	Optical characterization of CuInSe <sub>2</sub> single crystals prepared by travelling heater method. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2006</b> , 203, 2897-2903	1.6	8
130	In Situ Monitoring of GaN Reactive Ion Etching by Optical Emission Spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, L313-L315	1.4	8
129	Seeded growth of CuGaSe <sub>2</sub> single crystals using the travelling heater method. <i>Journal of Crystal Growth</i> , <b>1992</b> , 125, 381-383	1.6	8
128	AlGa <sub>N</sub> Channel High Electron Mobility Transistors with Regrown Ohmic Contacts. <i>Electronics (Switzerland)</i> , <b>2021</b> , 10, 635	2.6	8
127	High-temperature photoluminescence and photoluminescence excitation spectroscopy of Al <sub>0.60</sub> Ga <sub>0.40</sub> N/Al <sub>0.70</sub> Ga <sub>0.30</sub> N multiple quantum wells. <i>Applied Physics Express</i> , <b>2017</b> , 10, 021002	2.4	7
126	Curvature-controllable and crack-free AlN/sapphire templates fabricated by sputtering and high-temperature annealing. <i>Journal of Crystal Growth</i> , <b>2019</b> , 512, 131-135	1.6	7
125	Crystalline quality improvement of face-to-face annealed MOVPE-grown AlN on vicinal sapphire substrate with sputtered nucleation layer. <i>Journal of Crystal Growth</i> , <b>2020</b> , 545, 125722	1.6	7



124	Binding energy of localized biexcitons in AlGa <sub>N</sub> -based quantum wells. <i>Applied Physics Express</i> , <b>2014</b> , 7, 122101	2.4	7
123	Fabrication of crack-free thick AlN film on a-plane sapphire by low-pressure HVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 576-579		7
122	HVPE growth of thick AlN on trench-patterned substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 1483-1486		7
121	In-plane electric field induced by polarization and lateral photovoltaic effect in a-plane GaN. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 231102	3.4	7
120	In-plane structural anisotropy and polarized Raman-active mode studies of nonpolar AlN grown on 6H-SiC by low-pressure hydride vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 490-494	1.6	7
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117	Solution growth of CuInSe <sub>2</sub> from CuSe solutions. <i>Journal of Crystal Growth</i> , <b>1995</b> , 156, 404-409	1.6	7
116	Solution growth of CuGaS <sub>2</sub> and CuGaSe <sub>2</sub> using CuI solvent. <i>Journal of Crystal Growth</i> , <b>1993</b> , 130, 383-388	1.6	7
115	Polarity inversion of aluminum nitride by direct wafer bonding. <i>Applied Physics Express</i> , <b>2018</b> , 11, 031003	2.4	6
114	Microstructural analysis of an epitaxial AlN thick film/trench-patterned template by three-dimensional reciprocal lattice space mapping technique. <i>Applied Physics Express</i> , <b>2016</b> , 9, 111001	2.4	6
113	Properties of GaN grown on Si(111) substrates dependent on the thickness of 3C-SiC intermediate layers. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 063102	2.5	6
112	HVPE growth of c-plane AlN on a-plane sapphire using nitridation layer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 470-472		6
111	Fabrication of a binary diffractive lens for controlling the luminous intensity distribution of LED light. <i>Optical Review</i> , <b>2009</b> , 16, 455-457	0.9	6
110	Growth of CuGaS <sub>2</sub> single crystals by the traveling heater method using CuI solvent. <i>Journal of Crystal Growth</i> , <b>1994</b> , 144, 236-242	1.6	6
109	High-Quality AlN Template Prepared by Face-to-Face Annealing of Sputtered AlN on Sapphire. <i>Physica Status Solidi (B): Basic Research</i> , <b>2021</b> , 258, 2000352	1.3	6
108	Solution growth of chalcopyrite compounds single crystal. <i>Renewable Energy</i> , <b>2015</b> , 79, 127-130	8.1	5
107	Transient photoluminescence of aluminum-rich (Al,Ga)N low-dimensional structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 765-768	1.6	5

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104	Recombination dynamics of localized excitons in Al <sub>x</sub> Ga <sub>1-x</sub> N (0.37). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 2133-2135		5
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99	Improved optical properties using self-organized GaN nanotip structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2003</b> , 2566-2569		5
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97	Individually resolved luminescence from closely stacked GaN/AlN quantum wells. <i>Photonics Research</i> , <b>2020</b> , 8, 610	6	5
96	Microscopic potential fluctuations in Si-doped AlGa <sub>N</sub> epitaxial layers with various AlN molar fractions and Si concentrations. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 025707	2.5	5
95	Growth of Si-doped AlN on sapphire (0001) via pulsed sputtering. <i>APL Materials</i> , <b>2018</b> , 6, 111103	5.7	5
94	Low-threshold-current (~85 mA) of AlGa <sub>N</sub> -based UV-B laser diode with refractive-index waveguide structure. <i>Applied Physics Express</i> , <b>2021</b> , 14, 094009	2.4	5
93	Excitation and deexcitation dynamics of excitons in a GaN film based on the analysis of radiation from high-order states. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 245102	3	4
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